

May 2002 Revised May 2002

# 74LVT322373 • 74LVTH322373 Low Voltage 32-Bit Transparent Latch with 3-STATE Outputs and 25Ω Series Resistors in the Outputs

## **General Description**

The LVT322373 and LVTH322373 contain thirty-two non-inverting latches with 3-STATE outputs and are intended for bus oriented applications. The device is byte controlled. The flip-flops appear transparent to the data when the Latch Enable (LE) is HIGH. When LE is LOW, the data that meets the setup time is latched. Data appears on the bus when the Output Enable ( $\overline{\text{OE}}$ ) is LOW. When  $\overline{\text{OE}}$  is HIGH, the outputs are in a high impedance state.

The LVTH322373 data inputs include bushold, eliminating the need for external pull-up resistors to hold unused inputs.

These latches are designed for low voltage (3.3V)  $V_{CC}$  applications, but with the capability to provide a TTL interface to a 5V environment. The LVT322373 and LVTH322373 are fabricated with an advanced BiCMOS technology to achieve high speed operation similar to 5V ABT while maintaining a low power dissipation.

## **Features**

- $\blacksquare$  Input and output interface capability to systems at 5V  $V_{CC}$
- Bushold data inputs eliminate the need for external pull-up resistors to hold unused inputs (74LVTH322373), also available without bushold feature (74LVT322373)
- Live insertion/extraction permitted
- Power Up/Down high impedance provides glitch-free bus loading
- $\blacksquare$  Outputs include equivalent series resistance of  $25\Omega$  to make external termination resistors unnecessary and reduce overshoot and undershoot
- ESD performance:

Human-body model > 2000V

Machine model > 200V

Charged-device model > 1000V

■ Packaged in plastic Fine-Pitch Ball Grid Array (FBGA)

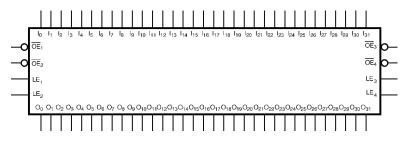
### **Ordering Code:**

Order Number	Package Number	Package Description
74LVT322373G (Note 1) (Note 2)	BGA96A (Preliminary)	96-Ball Fine-Pitch Ball Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide
74LVTH322373G (Note 1) (Note 2)	BGA96A	96-Ball Fine-Pitch Ball Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide

Note 1: Ordering Code "G" indicates Trays.

Note 2: Devices also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.

## **Logic Symbol**



# **Connection Diagram**

	1	2	3	4	5	6
٧	0	0	o	o	o	0
В		Õ				
ပ	0	0	0	0	0	0
О	0	0	0	0	0	O
ш	0	0	0	0	0	0
ட	0	0	0	0	0	0
Q	0	0	O	0	0	0
I	0	0	0	0	0	0
7	0	0	0	0	0	0
¥	0	0	0	0	0	0
_	0	0	0	0	0	0
Σ	0	0	O	0	0	0
z	0	0	Q	0	0	0
Ъ	0	0	0	0	0	0
Я	0	0	0	0	0	0
<b>-</b>	0	0	0	0	0	0

(Top Thru View)

# **Pin Descriptions**

Pin Names	Description
$\overline{OE}_n$	Output Enable Input (Active LOW)
LE <sub>n</sub>	Latch Enable Input
I <sub>0</sub> –I <sub>31</sub>	Inputs
O <sub>0</sub> -O <sub>31</sub>	3-STATE Outputs

# **FBGA Pin Assignments**

	1	2	3	4	5	6
Α	O <sub>1</sub>	O <sub>0</sub>	OE <sub>1</sub>	LE <sub>1</sub>	I <sub>0</sub>	I <sub>1</sub>
В	O <sub>3</sub>	O <sub>2</sub>	GND	GND	l <sub>2</sub>	l <sub>3</sub>
С	O <sub>5</sub>	O <sub>4</sub>	V <sub>CC1</sub>	V <sub>CC1</sub>	I <sub>4</sub>	I <sub>5</sub>
D	O <sub>7</sub>	O <sub>6</sub>	GND	GND	I <sub>6</sub>	I <sub>7</sub>
Е	O <sub>9</sub>	Ο <sub>8</sub>	GND	GND	I <sub>8</sub>	l <sub>9</sub>
F	O <sub>11</sub>	O <sub>10</sub>	V <sub>CC1</sub>	V <sub>CC1</sub>	I <sub>10</sub>	I <sub>11</sub>
G	O <sub>13</sub>	O <sub>12</sub>	GND	GND	I <sub>12</sub>	I <sub>13</sub>
Н	O <sub>14</sub>	O <sub>15</sub>	OE <sub>2</sub>	LE <sub>2</sub>	I <sub>15</sub>	I <sub>14</sub>
J	O <sub>17</sub>	O <sub>16</sub>	OE <sub>3</sub>	LE <sub>3</sub>	I <sub>16</sub>	I <sub>17</sub>
K	O <sub>19</sub>	O <sub>18</sub>	GND	GND	I <sub>18</sub>	I <sub>19</sub>
L	O <sub>21</sub>	O <sub>20</sub>	$V_{CC2}$	$V_{CC2}$	I <sub>20</sub>	l <sub>21</sub>
М	O <sub>23</sub>	O <sub>22</sub>	GND	GND	l <sub>22</sub>	l <sub>23</sub>
N	O <sub>25</sub>	O <sub>24</sub>	GND	GND	l <sub>24</sub>	l <sub>25</sub>
Р	O <sub>27</sub>	O <sub>26</sub>	$V_{CC2}$	$V_{CC2}$	I <sub>26</sub>	l <sub>27</sub>
R	O <sub>29</sub>	O <sub>28</sub>	GND	GND	I <sub>28</sub>	l <sub>29</sub>
Т	O <sub>30</sub>	O <sub>31</sub>	OE <sub>4</sub>	LE <sub>4</sub>	I <sub>31</sub>	I <sub>30</sub>

### **Truth Table**

	Inputs		Outputs
LE <sub>1</sub>	OE <sub>1</sub>	I <sub>0</sub> -I <sub>7</sub>	O <sub>0</sub> -O <sub>7</sub>
Х	Н	Х	Z
Н	L	L	L
Н	L	Н	Н
L	L	Χ	$O_0$
	Inputs		Outputs
LE <sub>3</sub>	OE <sub>3</sub>	I <sub>16</sub> -I <sub>23</sub>	O <sub>16</sub> -O <sub>23</sub>
Χ	Н	Х	Z
Н	L	L	L
Н	L	Н	Н
L	L	X	O <sub>0</sub>

	Inputs		Outputs
LE <sub>2</sub>	OE <sub>2</sub>	I <sub>8</sub> -I <sub>15</sub>	O <sub>8</sub> -O <sub>15</sub>
Х	Н	Χ	Z
Н	L	L	L
Н	L	Н	Н
L	L	Χ	$O_0$
	Inputs		Outputs
LE <sub>4</sub>	OE <sub>4</sub>	I <sub>24</sub> –I <sub>31</sub>	O <sub>24</sub> -O <sub>31</sub>
Х	Н	Х	Z
Н	L	L	L
Н	L	Н	Н
H L	L L	H X	Н О <sub>0</sub>

 $H = HIGH\ Voltage\ Level \qquad X = Immaterial \qquad Z = HIGH\ Impedance \qquad O_o = Previous\ O_o\ prior\ to\ HIGH-to-LOW\ transition\ of\ LEVE = Immaterial \qquad Immaterial \qquad$ 

## **Functional Description**

The LVT322373 and LVTH322373 contain thirty-two D-type latches with 3-STATE standard outputs. The device is byte controlled with each byte functioning identically, but independent of the other. Control pins can be shorted together to obtain full 32-bit operation. The following description applies to each byte. When the Latch Enable (LE<sub>n</sub>) input is HIGH, data on the D<sub>n</sub> enters the latches. In this condition the latches are transparent, i.e, a latch output will change states each time its D input changes. When LE<sub>n</sub> is LOW, the latches store information that was present on the D inputs a setup time preceding the HIGH-to-LOW transition of LE<sub>n</sub>. The 3-STATE standard outputs are controlled by the Output Enable ( $\overline{OE}_n$ ) input. When  $\overline{OE}_n$  is LOW, the standard outputs are in the 2-state mode. When  $\overline{OE}_n$  is HIGH, the standard outputs are in the high impedance mode but this does not interfere with entering new data into the latches.

# **Logic Diagrams** Byte 1 (0:7) Byte 2 (8:15) Byte 3 (16:23) Byte 4 (24:31)

 $\rm V_{\rm CC1}$  is associated with Bytes 1 and 2.

 $\rm V_{\rm CC2}$  is associated with Bytes 3 and 4.

Note: Please note that these diagrams are provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Symbol	Parameter	Value	Conditions	Units
V <sub>CC</sub>	Supply Voltage	-0.5 to +4.6		V
VI	DC Input Voltage	-0.5 to +7.0		V
Vo	DC Output Voltage	-0.5 to +7.0	Output in 3-STATE	V
		-0.5 to +7.0	Output in HIGH or LOW State (Note 4)	V
I <sub>IK</sub>	DC Input Diode Current	-50	V <sub>I</sub> < GND	mA
I <sub>OK</sub>	DC Output Diode Current	-50	V <sub>O</sub> < GND	mA
I <sub>O</sub>	DC Output Current	64	V <sub>O</sub> > V <sub>CC</sub> Output at HIGH State	mA
		128	V <sub>O</sub> > V <sub>CC</sub> Output at LOW State	IIIA
I <sub>CC</sub>	DC Supply Current per Supply Pin	±64		mA
I <sub>GND</sub>	DC Ground Current per Ground Pin	±128		mA
T <sub>STG</sub>	Storage Temperature	-65 to +150		°C

# **Recommended Operating Conditions**

Symbol	Parameter		Max	Units
V <sub>CC</sub>	Supply Voltage	2.7	3.6	V
VI	Input Voltage	0	5.5	V
I <sub>OH</sub>	HIGH Level Output Current		-12	mA
I <sub>OL</sub>	LOW Level Output Current		12	mA
T <sub>A</sub>	Free-Air Operating Temperature	-40	85	°C
Δt/ΔV	Input Edge Rate, V <sub>IN</sub> = 0.8V to 2.0V, V <sub>CC</sub> = 3.0V	0	10	ns/V

Note 3: Absolute Maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum rated conditions is not implied.

Note 4: Io Absolute Maximum Rating must be observed.

## **DC Electrical Characteristics**

Symbol	Parameter		V <sub>CC</sub>	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		Units	Conditions	
Syllibol	Farameter	i diametei		Min	Max	Ullis	Conditions	
V <sub>IK</sub>	Input Clamp Diode Voltage		2.7		-1.2	V	I <sub>I</sub> = -18 mA	
V <sub>IH</sub>	Input HIGH Voltage		2.7 - 3.6	2.0		V	$V_0 \le 0.1V$ or	
V <sub>IL</sub>	Input LOW Voltage		2.7 - 3.6		0.8	V	$V_O \ge V_{CC} - 0.1V$	
V <sub>OH</sub>	Output HIGH Voltage		2.7 - 3.6	V <sub>CC</sub> - 0.2		V	$I_{OH} = -100 \mu A$	
			3.0	2.0		V	$I_{OH} = -12 \text{ mA}$	
V <sub>OL</sub>	Output LOW Voltage		2.7		0.2	V	$I_{OL} = 100 \mu A$	
			3.0		0.8	V	I <sub>OL</sub> = 12 mA	
I(HOLD)	Bushold Input Minimum Drive		3.0	75		μΑ	$V_{I} = 0.8V$	
			3.0	-75			$V_1 = 2.0V$	
I(OD)	Bushold Input Over-Drive		3.0	500		μА	(Note 5)	
	Current to Change State		3.0	-500		μА	(Note 6)	
ı	Input Current		3.6		10		$V_1 = 5.5V$	
		Control Pins	3.6		±1	μА	$V_I = 0V \text{ or } V_{CC}$	
		Data Pins	3.6		-5	μΛ	$V_I = 0V$	
					1		$V_I = V_{CC}$	
OFF	Power Off Leakage Current		0		±100	μΑ	$0V \le V_I \text{ or } V_O \le 5.5V$	
PU/PD	Power up/down 3-STATE		0 - 1.5V		±100	μА	$V_0 = 0.5V \text{ to } 3.0V$	
	Output Current		0 - 1.50		±100	μА	$V_I = GND \text{ or } V_{CC}$	
OZL	3-STATE Output Leakage Current		3.6		-5	μΑ	V <sub>O</sub> = 0.5V	
lozн	3-STATE Output Leakage Current		3.6		5	μΑ	$V_0 = 3.0V$	
OZH <sup>+</sup>	3-STATE Output Leakage Current		3.6		10	μΑ	$V_{CC} < V_O \le 5.5V$	
ССН	Power Supply Current	(V <sub>CC1</sub> or V <sub>CC2</sub> )	3.6		0.19	mA	Outputs HIGH	
CCL	Power Supply Current	(V <sub>CC1</sub> or V <sub>CC2</sub> )	3.6		5	mA	Outputs LOW	
I <sub>CCZ</sub>	Power Supply Current	(V <sub>CC1</sub> or V <sub>CC2</sub> )	3.6	j	0.19	mA	Outputs Disabled	

## DC Electrical Characteristics (Continued)

Symbol	Parameter		v <sub>cc</sub>	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		Units	Conditions	
Cymbol			(V)	Min	Max	Omia	Conditions	
I <sub>CCZ</sub> +	Power Supply Current	(V <sub>CC1</sub> or V <sub>CC2</sub> )	3.6		0.19	mA	$V_{CC} \le V_O \le 5.5V$ ,	
							Outputs Disabled	
$\Delta I_{CC}$	Increase in Power Supply Current	(V <sub>CC1</sub> or V <sub>CC2</sub> )	3.6		0.2	mA	One Input at V <sub>CC</sub> – 0.6V	
	(Note 7)						Other Inputs at V <sub>CC</sub> or GND	

Note 5: An external driver must source at least the specified current to switch from LOW-to-HIGH.

Note 6: An external driver must sink at least the specified current to switch from HIGH-to-LOW.

Note 7: This is the increase in supply current for each input that is at the specified voltage level rather than  $V_{CC}$  or GND.

# **Dynamic Switching Characteristics** (Note 8)

Symbol	Parameter	v <sub>cc</sub>	T <sub>A</sub> = 25°C			Units	Conditions	
Syllibol	i arameter	(V)	Min	Тур	Max	Omits	$ extsf{C}_{ extsf{L}} =  extsf{500}\Omega$	
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	3.3		0.8		V	(Note 9)	
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	3.3		-0.8		V	(Note 9)	

Note 8: Characterized in SSOP package. Guaranteed parameter, but not tested.

Note 9: Max number of outputs defined as (n). n-1 data inputs are driven 0V to 3V. Output under test held LOW.

### **AC Electrical Characteristics**

		T <sub>A</sub> :	$T_A = -40$ °C to +85°C, $C_L = 50$ pF, $R_L = 500\Omega$					
Symbol	Parameter	V <sub>CC</sub> = 3.	.3V ± 0.3V	V <sub>cc</sub>	Units			
		Min	Max	Min	Max	1		
t <sub>PHL</sub>	Propagation Delay	1.3	4.8	1.3	5.3	ns		
t <sub>PLH</sub>	D <sub>n</sub> to O <sub>n</sub>	1.4	4.8	1.4	5.1	ns		
t <sub>PHL</sub>	Propagation Delay	1.7	5.0	1.7	5.1	ns		
t <sub>PLH</sub>	LE to O <sub>n</sub>	1.4	5.1	1.4	5.8	115		
t <sub>PZL</sub>	Output Enable Time	1.6	5.0	1.6	6.0	ns		
t <sub>PZH</sub>		1.0	5.4	1.0	6.6	115		
t <sub>PLZ</sub>	Output Disable Time	1.6	5.1	1.6	5.0	ns		
t <sub>PHZ</sub>		1.8	5.4	1.8	5.7	115		
t <sub>S</sub>	Setup Time, D <sub>n</sub> to LE	1.0		0.8		ns		
t <sub>H</sub>	Hold Time, D <sub>n</sub> to LE	1.0		1.1		ns		
t <sub>W</sub>	LE Pulse Width	3.0		3.0		ns		
toshl	Output to Output Skew (Note 10)		1.0		1.0	ns		
t <sub>OSLH</sub>			1.0		1.0	115		

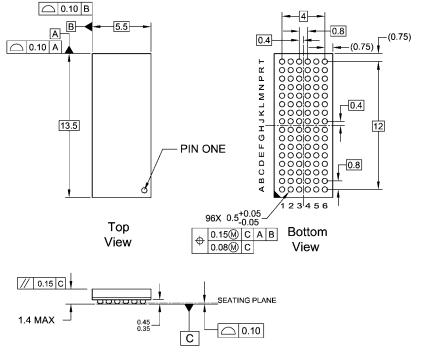
Note 10: Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t<sub>OSHL</sub>) or LOW-to-HIGH (t<sub>OSLH</sub>).

# Capacitance (Note 11)

Symbol	Parameter	Conditions	Typical	Units
C <sub>IN</sub>	Input Capacitance	$V_{CC} = Open, V_I = 0V \text{ or } V_{CC}$	4	pF
C <sub>OUT</sub>	Output Capacitance	$V_{CC} = 3.0V$ , $V_{O} = 0V$ or $V_{CC}$	8	pF

Note 11: Capacitance is measured at frequency f = 1 MHz, per MIL-STD-883, Method 3012.

# Physical Dimensions inches (millimeters) unless otherwise noted



### NOTES:

- A. THIS PACKAGE CONFORMS TO JEDEC M0-205
- B. ALL DIMENSIONS IN MILLIMETERS
- C. LAND PATTERN RECOMMENDATION: NSMD (Non Solder Mask Defined)
  .35MM DIA PADS WITH A SOLDERMASK OPENING OF .45MM CONCENTRIC TO PADS
  D. DRAWING CONFORMS TO ASME Y14.5M-1994

BGA96ArevE

96-Ball Fine-Pitch Ball Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide Package Number BGA96A **Preliminary** 

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